

Number	Hit	Search Text	DB	Time Stamp
1	27	condem33 near wall32; same (hole holes opening aperture near through)	USPAT; EPO; JPO; DERWENT	2003/01/10 08:16
2	28	condem33 near wall32; same (hole holes opening aperture near through with wafer substrate)	USPAT; EPO; JPO; DERWENT	2003/01/10 08:14
3	28	condem33 near wall32; same (hole holes opening aperture near through); not (condem33 near wall32) same (hole holes opening aperture near through with wafer substrate)	USPAT; EPO; JPO; DERWENT	2003/01/10 08:14
5	35	(condem33 near wall32) same (hole holes opening aperture near through); not (condem33 near wall32) same (hole holes opening aperture near through) with (wafer substrate); and (plasma semiconductor ("1474-12").PN.	USPAT; EPO; JPO; DERWENT	2003/01/10 09:11
6	1	"1474-12".PN.	USPAT; EPO; JPO; USPAT; EPO; JPO; USPAT; EPO; JPO; JP; DERWENT	2003/01/10 10:11 2003/01/10 10:11 2003/01/10 10:12 2003/01/09 12:46 2003/01/09 12:51
7	9	"60517".	JP; DERWENT	2003/01/09 13:20
8	2	"130181.5".	JP; DERWENT	2003/01/09 12:51
	119908	h01.163.1pc. c13c0163.1pc.	JP; DERWENT	2003/01/09 12:53
	18640	(h01.163.1pc. c13c0163.1pc.) and (electrode anode; same mov33 lower33)	JP; DERWENT	2003/01/09 13:11
	24468	(h01.163.1pc. c13c0163.1pc.) and (electrode susceptor holder chuck) same (mov33 lower33)	JP; DERWENT	2003/01/09 13:12
	14536	(h01.163.1pc. c13c0163.1pc.) and (electrode anode) with (mov33 lower33)	JP; DERWENT	2003/01/09 13:12
	18779	(h01.163.1pc. c13c0163.1pc.) and (electrode susceptor holder chuck) with (mov33 lower33)	JP; DERWENT	2003/01/09 13:12
	21	suscep-tcmk18.in.	JP; DERWENT	2003/01/09 13:12
	38	masa-koichi.3.in.	JP; DERWENT	2003/01/09 13:12
	836	crn-takeshi.3.in.	JP; DERWENT	2003/01/09 13:19
	12249	"tokyo electron".as.	USPAT; US-PGUB; JP; DERWENT	2003/01/09 14:06
	23	sten-wa-tomck18.in.	JP; DERWENT	2003/01/09 13:12
	1014	crn-takeshi.3.in.	JP; DERWENT	2003/01/09 13:12
	32	masa-koichi.3.in.	JP; DERWENT	2003/01/09 13:18
	21	masa-koichi.3.in. not sus-ma-tomck18.in.	JP; DERWENT	2003/01/09 13:18
	4	sten-wa-tomck18.in. not sus-ma-tomck18.in.	JP; DERWENT	2003/01/09 13:19
	3	crn-takeshi.3.in. and "tokyo electron".as.	JP; DERWENT	2003/01/09 13:19
	1389	"tokyo electron".as.	US-PGUB; JP; DERWENT	2003/01/09 15:49



14192	"toxya electron".as.	USPAT; EPO; JPO; DERWENT	2003/01/09 15:49
11104	"toxya electron".as. and HO113213.ipc. 823.0148.ipc.	USPAT; EPO; JPO; DERWENT	2003/01/09 15:49
21	tanaka-tanaka@3.in.	USPAT; EPO; JPO; DERWENT	2003/01/09 16:05
11	"4285 12" "3963145" "5067145" "51104 1" "5116450" "5272417" "53310 0" "5332852" "5319432" "50492 1" "5113736".PN.	USPAT; EPO; JPO; DERWENT	2003/01/09 16:01
1306563	cover	USPAT; EPO; JPO; DERWENT	2003/01/09 16:08
2469	bellows near5 cover	USPAT; EPO; JPO; DERWENT	2003/01/09 16:06
9	bellows near5 cover) and ((HO1021\$.ipc. (HO1021\$.ipc.) and (electrode susceptor HO1021\$.ipc.) same (HO1021\$.ipc.)	USPAT; EPO; JPO; DERWENT	2003/01/09 16:06
14	"69125"	USPAT; EPO; JPO; DERWENT	2003/01/09 16:24
3	"061074"	USPAT; EPO; JPO; DERWENT	2003/01/09 16:25
2	"1047458"	USPAT; EPO; JPO; DERWENT	2003/01/09 16:28
3	"7410776"	USPAT; EPO; JPO; DERWENT	2003/01/09 16:42
1450	conduct33 near wall12) same (hole holes aperture	USPAT; EPO; JPO; DERWENT	2003/01/09 16:56
49	conduct33 near wall12) same (hole holes aperture and HO113213.ipc. HO113213.ipc.)	USPAT; EPO; JPO; DERWENT	2003/01/09 16:47
4	conduct33 near wall12) same (hole holes aperture) and (118/729.ccls. 118/729.ccls.)	USPAT; EPO; JPO; DERWENT	2003/01/09 16:52
12	"106172" "5099100" "5213659" " "106172" "5234525" "5246532" " "106172" "5334351" "5344488" " "106172" "5334751" "5351124".PN.	USPAT; EPO; JPO; DERWENT	2003/01/10 08:56
2	conduct33 near wall12) same (hole holes aperture) same (wafer substrate) near carrier transfer)	USPAT; EPO; JPO; DERWENT	2003/01/09 17:19
99	158/315.31.ccls.		